

Attorney Docket No.: 5308-389

PATENT



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re: Saxler

Confirmation No.: 8522

Application No.: 10/772,882

Group Art Unit: 2811

Filed: February 5, 2004

Examiner Name: Jerome Jackson, Jr.

For: NITRIDE HETEROJUNCTION TRANSISTORS HAVING CHARGE-TRANSFER
INDUCED ENERGY BARRIERS AND METHODS OF FABRICATING THE SAME.

Date: February 24, 2005

Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. § 1.97(b)

Sir:

Attached is a list of documents on Form PTO-1449. A copy of any listed U.S. patent and/or U.S. patent application publication is not provided herewith in accordance with the waiver by the U.S. Patent and Trademark Office of requirements under 37 C.F.R. § 1.98(a)(2)(i) for all U.S. national patent applications filed after June 30, 2003 and for all international applications that have entered the national stage under 35 USC § 371 after June 30, 2003. It is requested that these documents be considered by the Examiner and officially made of record in accordance with the provisions of 37 C.F.R. § 1.56 and Section 609 of the MPEP.

This Information Disclosure Statement is submitted in accordance with 37 C.F.R. § 1.97(b), within three months of the filing date of the above-referenced application or before the mailing of a first Office Action on the merits, whichever event occurs last. Therefore, no fee is believed due. However, the Commissioner is hereby authorized to charge any deficiency or credit any overpayment to Deposit Account No. 50-0220.

Respectfully submitted,

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I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to: Mail Stop Amendment, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on February 24, 2005.

Traci A. Brown

Form PTO-1449		U.S. Department of Commerce Patent and Trademark Office		Attorney Docket No. 5308-389		Serial No. 10 772.882	
LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary)				Applicant: Saxler			
				Filing Date: February 5, 2004		GAU: 2811	
U.S. PATENT DOCUMENTS							
Examiner Initials		Document No.	Date (m d y)	Name	Class	Subclass	Filing Date if Appropriate
	1.	6,150,680	11/21/00	Eastman et al.	257	224	
	2.	2003/0123829 A1	07/03/03	Taylor	385	131	
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Subclass	Translation (Yes/No)
	3.	11261053	09/24/99	Japan	H01L	29/778	Abstract/No
	4.	2004/008495 A2/A3	01/22/04	PCT	H01L	21/335	
	5.	0 334 006 A1	09/27/89	EPO	H01L	29/80	
OTHER DOCUMENTS							
	6.	Chang et al., "AlGaIn/GaN Modulation-Doped Field-Effect Transistors with an Mg-doped Carrier Confinement Layer," <i>Jpn. J. Appl. Phys.</i> , 42:3316-3319 (2003).					
	7.	Cho et al., "A New GaAs Field Effect Transistor (FET) with Dipole Barrier (DIB)," <i>Jpn. J. Appl. Phys.</i> 33:775-778 (1994).					
	8.	Coffie et al., "Unpassivated p-GaN/AlGaIn/GaN HEMTs with 7.1 W/MMF at 10 GHz," <i>Electronic Letters online No. 20030872</i> , 39(19), (September 18, 2003).					
	9.	Küsters et al., "Double-Heterojunction Lattice-Matched and Pseudomorphic InGaAs HEMT with δ -Doped InP Supply Layers and p-InP Barrier Enhancement Layer Grown by LP-MOVPE," <i>IEEE Electron Device Letters</i> , 14(1), (January 1993).					
	10.	Shiojima et al., "Improved Carrier Confinement by a Buried p-Layer in the AlGaIn/GaN HEMT Structure," <i>IEICE Trans. Electron.</i> , E83-C(12), (December 2000).					
	11.	International Search Report and Written Opinion of the International Searching Authority for PCT US2004/031984; date of mailing January 21, 2005.					

Examiner: _____ Date Considered: _____

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.